| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 16 | @ad<=20011206 and 'silicon oxynitride' same 'silane' same 'dichlorosilane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/20 09:09 |
| 2 | 2 | @ad<=20011206 and 'SiON' same 'silane' same 'dichlorosilane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/20 09:07 |
| – | 696 | (438/400).ccls. and @ad<=20011206 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 11:22 |
| – | 6 | ((438/400).ccls. and @ad<=20011206) and ONO | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 11:26 |
| – | 0 | @ad<=20011206 and 'ONO structure' with 'buffer layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:35 |
| – | 290 | @ad<=20011206 and 'ONO structure' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:01 |
| – | 160 | @ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:31 |
| – | 3 | @ad<=20011206 and 'ONO structure' and 'buffer layer' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:40 |
| – | 1 | @ad<=20011206 and 'multi dielectric layer' and 'memory' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:43 |
| – | 26 | @ad<=20011206 and 'multi' adj 'dielectric' and 'memory' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:47 |
| – | 0 | @ad<=20011206 and 'O-SiON-N-SiON-O' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:49 |
| – | 1393 | @ad<=20011206 and oxide and SiON and Nitride and SiON and oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:55 |
| – | 0 | @ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 12:56 |

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|---|---|---|---|---|
| – | 300 | @ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 14:31 |
| – | 107 | (@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') and memory | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 14:52 |
| – | 540 | @ad<=20011206 and (438/778).ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/17 14:32 |
| – | 2862 | ((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 08:49 |
| – | 2356 | ((257/324) or (257/314-315) or (257/406) or (257/410)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 08:41 |
| – | 7 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'silane' with 'nitrogen oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 08:59 |
| – | 6328 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'SiON' or 'silicon oxynitride' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:03 |
| – | 0 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and SiH4 with N2O with NH3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:04 |
| – | 8 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'SiON' with 'deposition' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:09 |
| – | 448 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'ammonia' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:11 |
| – | 190 | (((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'ammonia' and 'silane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:11 |
| – | 194 | @ad<=20011206 and 'ammonia' and 'silane' and 'nitrogen oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:16 |
| – | 359 | @ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:27 |
| – | 27 | @ad<=20011206 and 'ammonia' same 'silane' same 'nitrogen oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/10/28 09:19 |

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| - | 0 | @ad<=20011206 and 'oxide' same 'silane' same dichloro adj silane with 'nitrogen oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:29 |
|---|---|---|---|---|
| - | 0 | @ad<=20011206 and 'silane' same 'dichloro silane' with 'nitrogen oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:30 |
| - | 3 | @ad<=20011206 and 'silane' same 'dichlorosilane' with 'N.sub.20' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:36 |
| - | 0 | @ad<=20011206 and 'silicon oxide' same 'silane' same 'DCS' same 'N.sub.20' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:37 |
| - | 32 | @ad<=20011206 and 'silicon oxide' same 'silane' same 'N.sub.20' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/13 13:39 |
| - | 25 | @ad<=20011206 and 'silicon oxide' same 'silane' same 'nitrous oxide' and 'dichlorosilane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 10:17 |
| - | 71 | @ad<=20011206 and 'oxide' same 'silane' same 'nitrous oxide' same 'dichlorosilane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 10:51 |
| - | 12 | @ad<=20011206 and 'oxide' same 'SiH.sub.4' same 'N.sub.20' same 'SiH.sub.2Cl.sub.2' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 10:29 |
| - | 4 | @ad<=20011206 and 'silicon oxide' same 'SiH.sub.4' same 'N.sub.20' same 'SiH.sub.2Cl.sub.2' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 10:37 |
| - | 5 | (("6127255") or ("5811316") or ("5331191") or ("5202275")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 10:37 |
| - | 27 | @ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same 'dichlorosilane' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/20 09:06 |
| - | 160 | (@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') and memory | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 15:20 |
| - | 1 | "5506178".PN. | USPAT | 2003/06/19 15:06 |
| - | 45 | hisatomi-kiyoshi.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 15:25 |

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| - | 20 | toshiba.as. and 'ONO' and 'oxynitride' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 15:28 |
| - | 341 | toshiba.as. and 'oxynitride' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/06/19 15:29 |

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